

WE CLAIM:

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- sub A2
1. A method for forming a spacer, comprising:
 depositing an oxide layer over a polysilicon line of a core and periphery area;
 performing a first spacer in the core and periphery area;
 implanting an area located between polysilicon lines in the core area;
 applying a second oxide layer over the core and periphery areas; and
 performing a second spacer etch over the periphery area wherein a difference appearance of the core and periphery areas is produced.
 2. The method of claim 1 wherein the first oxide deposition has a thickness of less than one-half the distance between a periphery of the polysilicon lines.
 3. A non volatile memory device made by the method of claim 1.
 4. A non volatile memory device made by the method of claim 2.
- add A3

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